

# **PBHV9414ZX Datasheet**

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DiGi Electronics Part Number PBHV9414ZX-DG

Manufacturer Nexperia USA Inc.

Manufacturer Product Number PBHV9414ZX

Description TRANS PNP 140V 4A SOT223

**Detailed Description** Bipolar (BJT) Transistor PNP 140 V 4 A 650 mW Surfa

ce Mount SOT-223



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# **Purchase and inquiry**

Manufacturer Product Number:	Manufacturer:
PBHV9414ZX	Nexperia USA Inc.
Series:	Product Status:
	Active
Transistor Type:	Current - Collector (Ic) (Max):
PNP	4 A
Voltage - Collector Emitter Breakdown (Max):	Vce Saturation (Max) @ lb, lc:
140 V	550mV @ 400mA, 4A
Current - Collector Cutoff (Max):	DC Current Gain (hFE) (Min) @ Ic, Vce:
100nA	100 @ 10mA, 5V
Power - Max:	Frequency - Transition:
650 mW	
Operating Temperature:	Grade:
150°C (TJ)	Automotive
Qualification:	Mounting Type:
AEC-Q100	Surface Mount
Package / Case:	Supplier Device Package:
TO-261-4, TO-261AA	SOT-223
Base Product Number:	
PBHV9414	

# **Environmental & Export classification**

RoHS Status:	Moisture Sensitivity Level (MSL):
ROHS3 Compliant	1 (Unlimited)
REACH Status:	ECCN:
REACH Unaffected	EAR99
HTSUS:	
8541.21.0095	



# **PBHV9414Z**

# 140 V, 4 A PNP high-voltage low VCEsat (BISS) transistor 24 January 2014 Product data sheet

## 1. General description

PNP high-voltage low V<sub>CEsat</sub> Breakthrough Small Signal (BISS) transistor in a medium power SOT223 (SC-73) Surface-Mounted Device (SMD) plastic package.

#### 2. Features and benefits

- High voltage
- Low collector-emitter saturation voltage V<sub>CEsat</sub>
- High collector current capability I<sub>C</sub> and I<sub>CM</sub>
- High collector current gain h<sub>FE</sub> at high I<sub>C</sub>
- AEC-Q101 qualified

## 3. Applications

- LED driver for LED chain module
- LCD backlighting
- Automotive motor management
- Switch Mode Power Supply (SMPS)

#### 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>CEO</sub>	collector-emitter voltage	open base	-	-	-140	V
I <sub>C</sub>	collector current		-	-	-4	Α
I <sub>CM</sub>	peak collector current	single pulse; t <sub>p</sub> ≤ 1 ms	-	-	-10	Α
R <sub>CEsat</sub>	collector-emitter saturation resistance	$I_C$ = -1 A; $I_B$ = -100 mA; pulsed; $t_p \le 300$ μs; $\delta \le 0.02$ ; $T_{amb}$ = 25 °C	-	100	150	mΩ



140 V, 4 A PNP high-voltage low VCEsat (BISS) transistor

# 5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	В	base	4	2, 4
2	С	collector		1—
3	Е	emitter		
4	С	collector	⊟1 ⊟2 ⊟3 SC-73 (SOT223)	3 sym028

# 6. Ordering information

Table 3. Ordering information

Type number Package			
	Name	Description	Version
PBHV9414Z	SC-73	plastic surface-mounted package with increased heatsink; 4 leads	SOT223

# 7. Marking

Table 4. Marking codes

Type number	Marking code
PBHV9414Z	V9414Z

# 8. Limiting values

#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>CBO</sub>	collector-base voltage	open emitter		-	-180	V
V <sub>CEO</sub>	collector-emitter voltage	open base		-	-140	V
V <sub>EBO</sub>	emitter-base voltage	open collector		-	-7	V
I <sub>C</sub>	collector current			-	-4	Α
I <sub>CM</sub>	peak collector current	single pulse; t <sub>p</sub> ≤ 1 ms		-	-10	Α
I <sub>B</sub>	base current			-	-500	mA
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	[1]	-	0.65	W
			<u>[2]</u>	-	1	W
			<u>[3]</u>	-	1.35	W
T <sub>j</sub>	junction temperature			-	150	°C

PBHV9414Z

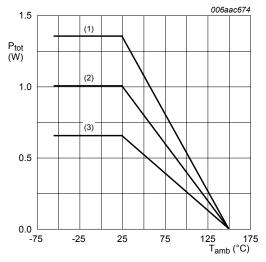
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#### 140 V, 4 A PNP high-voltage low VCEsat (BISS) transistor

Symbol	Parameter	Conditions	Min	Max	Unit
T <sub>amb</sub>	ambient temperature		-55	150	°C
T <sub>stg</sub>	storage temperature		-65	150	°C

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm<sup>2</sup>.
- [3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm<sup>2</sup>.



- (1) FR4 PCB, mounting pad for collector 6  ${\rm cm}^2$
- (2) FR4 PCB, mounting pad for collector 1 cm<sup>2</sup>
- (3) FR4 PCB, standard footprint

Fig. 1. Power derating curves

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140 V, 4 A PNP high-voltage low VCEsat (BISS) transistor

### 9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R <sub>th(j-a)</sub> thermal resistance from junction to ambient			[1]	-	-	192	K/W
		[2]	-	-	125	K/W	
	ambient		[3]	-	-	93	K/W
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point			-	-	16	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm<sup>2</sup>.
- [3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm<sup>2</sup>.

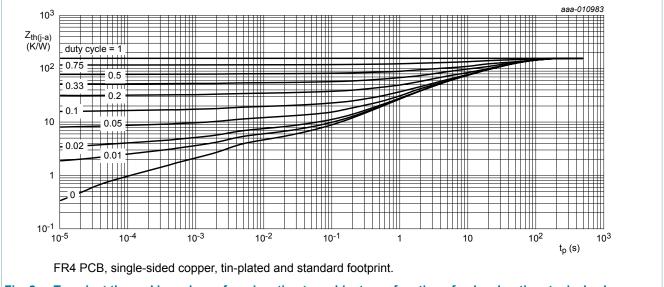
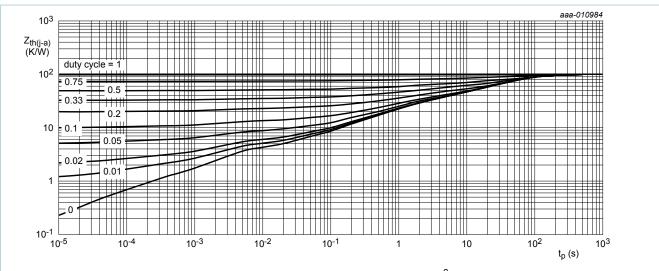


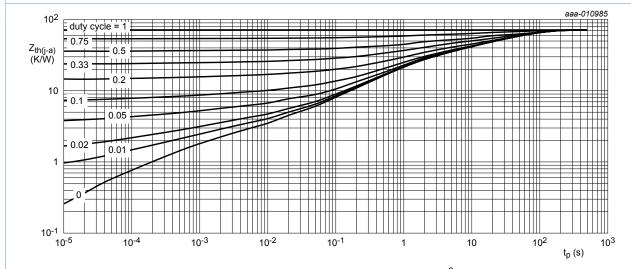
Fig. 2. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

#### 140 V, 4 A PNP high-voltage low VCEsat (BISS) transistor



FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm<sup>2</sup>

Fig. 3. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm<sup>2</sup>

Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

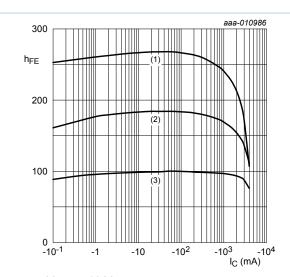
140 V, 4 A PNP high-voltage low VCEsat (BISS) transistor

# 10. Characteristics

#### Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I <sub>СВО</sub>	collector-base cut-off	V <sub>CB</sub> = -150 V; I <sub>E</sub> = 0 A; T <sub>amb</sub> = 25 °C	-	-	-100	nA
	current	V <sub>CB</sub> = -150 V; I <sub>E</sub> = 0 A; T <sub>j</sub> = 150 °C	-	-	-50	μΑ
CES	collector-emitter cut-off current	V <sub>CE</sub> = -115 V; V <sub>BE</sub> = 0 V; T <sub>amb</sub> = 25 °C	-	-	-100	nA
EBO	emitter-base cut-off current	V <sub>EB</sub> = -6 V; I <sub>C</sub> = 0 A; T <sub>amb</sub> = 25 °C	-	-	-100	nA
ı <sub>FE</sub>	DC current gain	$V_{CE}$ = -5 V; $I_{C}$ = -10 mA; $T_{amb}$ = 25 °C	100	160	-	
		$V_{CE} = -5 \text{ V; } I_{C} = -1 \text{ A; pulsed;}$ $t_{p} \le 300 \text{ µs; } \delta \le 0.02 \text{ ; } T_{amb} = 25 \text{ °C}$	100	150	300	
		$V_{CE}$ = -5 V; $I_{C}$ = -3 A; pulsed; $t_{p} \le 300 \ \mu s; \ \delta \le 0.02 \ ; \ T_{amb}$ = 25 °C	75	100	-	
		$V_{CE}$ = -5 V; $I_{C}$ = -4 A; pulsed; $t_{p} \le 300 \ \mu s; \ \delta \le 0.02 \ ; T_{amb}$ = 25 °C	35	50	-	
V <sub>CEsat</sub> collector-emitter saturation voltage	$I_{C}$ = -100 mA; $I_{B}$ = -5 mA; pulsed; $t_{p} \le 300 \ \mu s; \ \delta \le 0.02 \ ; \ T_{amb}$ = 25 °C	-	-45	-60	mV	
		$I_{C}$ = -500 mA; $I_{B}$ = -50 mA; pulsed; $t_{p} \le 300 \ \mu s; \ \delta \le 0.02 \ ; T_{amb}$ = 25 °C	-	-60	-100	mV
		$I_{C}$ = -1 A; $I_{B}$ = -100 mA; pulsed; $t_{p} \le 300 \ \mu s; \ \delta \le 0.02 \ ; T_{amb}$ = 25 °C	-	-100	-150	mV
		$I_{C}$ = -3 A; $I_{B}$ = -300 mA; $t_{p}$ ≤ 300 µs; $\delta$ ≤ 0.02 ; $T_{amb}$ = 25 °C; pulsed	-	-275	-370	mV
		$I_{C}$ = -4 A; $I_{B}$ = -400 mA; pulsed; $t_{p} \le 300 \ \mu s; \ \delta \le 0.02 \ ; T_{amb}$ = 25 °C	-	-420	-550	mV
R <sub>CEsat</sub>	collector-emitter saturation resistance	$I_{C}$ = -1 A; $I_{B}$ = -100 mA; pulsed; $t_{p} \le 300 \ \mu s; \ \delta \le 0.02 \ ; T_{amb}$ = 25 °C	-	100	150	mΩ
/ <sub>BEsat</sub>	base-emitter saturation voltage	$I_{C}$ = -1 A; $I_{B}$ = -100 mA; pulsed; $t_{p} \le 300 \ \mu s$ ; $\delta \le 0.02$ ; $T_{amb}$ = 25 °C	-	-	-1.2	V
/ <sub>BEon</sub>	base-emitter turn-on voltage	$V_{CE} = -5 \text{ V}; I_{C} = -1 \text{ A}; t_{p} \le 300 \mu\text{s};$ $\delta \le 0.02 ; T_{amb} = 25 °C; \text{ pulsed}$	-	-	-1.1	V

#### 140 V, 4 A PNP high-voltage low VCEsat (BISS) transistor



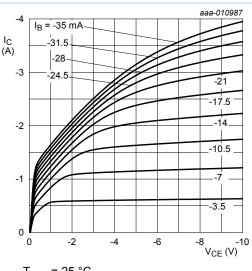
$$V_{CE} = -10 \text{ V}$$

(1) 
$$T_{amb} = 100 \, ^{\circ}C$$

(2) 
$$T_{amb}$$
 = 25 °C

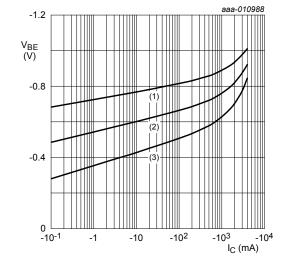
(3) 
$$T_{amb} = -55 \, ^{\circ}C$$

Fig. 5. DC current gain as a function of collector current; typical values



 $T_{amb} = 25 \, ^{\circ}C$ 

Fig. 6. Collector current as a function of collectoremitter voltage; typical values



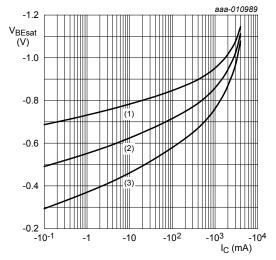
$$V_{CE} = -10 \text{ V}$$

(1) 
$$T_{amb} = -55 \, ^{\circ}C$$

(2) 
$$T_{amb}$$
 = 25 °C

(3) 
$$T_{amb} = 100 \, ^{\circ}C$$

Fig. 7. Base-emitter voltage as a function of collector current; typical values



$$I_{\rm C}/I_{\rm B} = 20$$

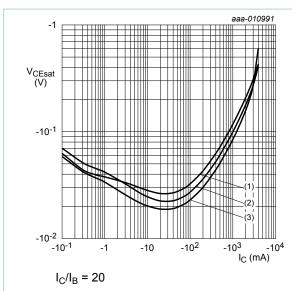
(1) 
$$T_{amb} = -55 \, ^{\circ}C$$

(2) 
$$T_{amb}$$
 = 25 °C

(3) 
$$T_{amb} = 100 \, ^{\circ}C$$

Fig. 8. Base-emitter saturation voltage as a function of collector current; typical values

#### 140 V, 4 A PNP high-voltage low VCEsat (BISS) transistor

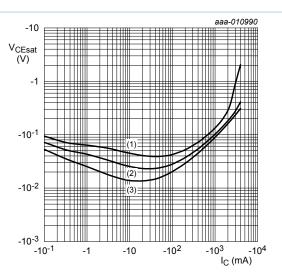


(1) 
$$T_{amb} = 100 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3) 
$$T_{amb} = -55$$
 °C

Fig. 9. Collector-emitter saturation voltage as a function of collector current; typical values



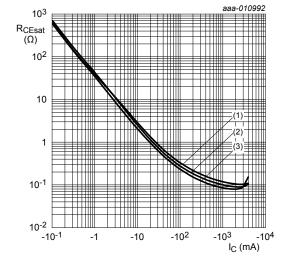
$$T_{amb} = 25 \, ^{\circ}C$$

(1) 
$$I_C/I_B = 20$$

(2) 
$$I_C/I_B = 10$$

(3) 
$$I_C/I_B = 5$$

Fig. 10. Collector-emitter saturation voltage as a function of collector current; typical values



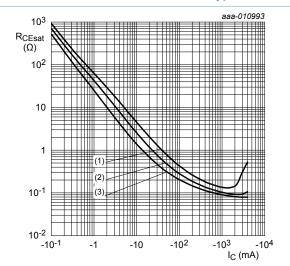
$$I_{\rm C}/I_{\rm B} = 20$$

(1) 
$$T_{amb} = 100 \, ^{\circ}C$$

(2) 
$$T_{amb}$$
 = 25 °C

(3) 
$$T_{amb} = -55$$
 °C

Fig. 11. Collector-emitter saturation resistance as a function of collector current; typical values



$$T_{amb} = 25 \, ^{\circ}C$$

(1) 
$$I_C/I_B = 20$$

(2) 
$$I_C/I_B = 10$$

(3) 
$$I_C/I_B = 5$$

Fig. 12. Collector-emitter saturation resistance as a function of collector current; typical values

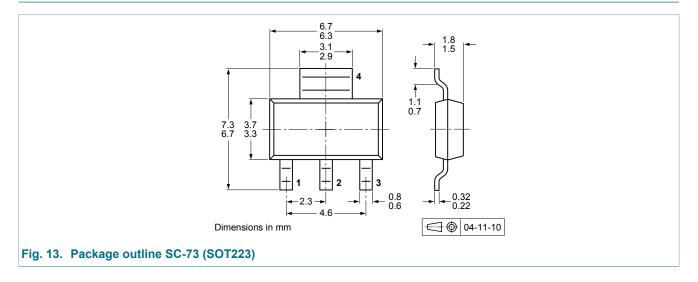
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## 11. Test information

#### 11.1 Quality information

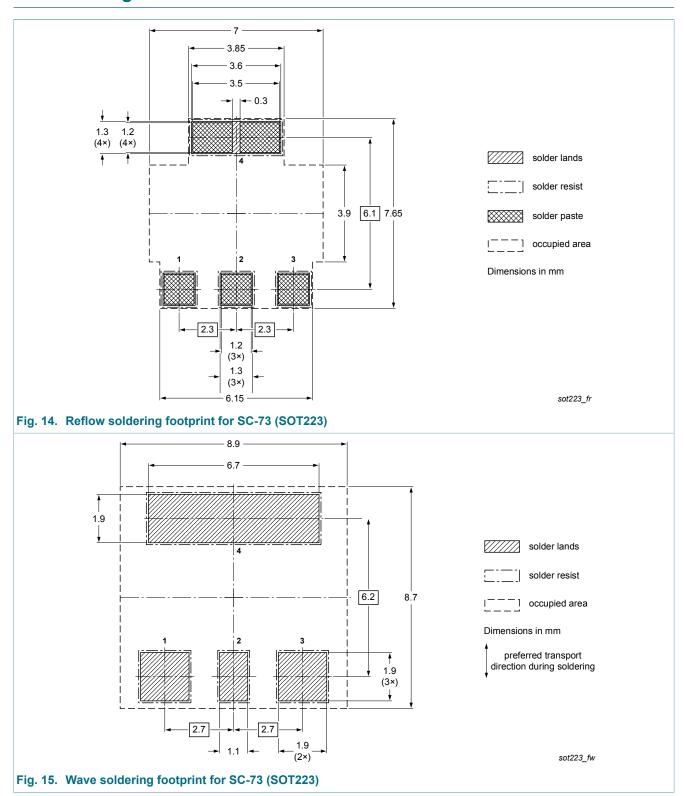
This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

# 12. Package outline



140 V, 4 A PNP high-voltage low VCEsat (BISS) transistor

# 13. Soldering



140 V, 4 A PNP high-voltage low VCEsat (BISS) transistor

# 14. Revision history

#### Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PBHV9414Z v.2	20140124	Product data sheet	-	PBHV9414Z v.1
Modifications:	Product status char	nged		
PBHV9414Z v.1	20131001	Objective data sheet	-	-

#### 140 V, 4 A PNP high-voltage low VCEsat (BISS) transistor

## 15. Legal information

#### 15.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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